2SB859

Silicon PNP Triple Diffused

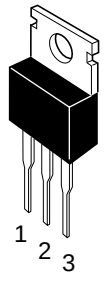
HITACHI

Application

Low frequency power amplifier complementary pair with 2SD1135

Outline

TO-220AB



1. Base
2. Collector (Flange)
3. Emitter

Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	Rating	Unit
Collector to base voltage	V_{CBO}	–100	V
Collector to emitter voltage	V_{CEO}	–80	V
Emitter to base voltage	V_{EBO}	–5	V
Collector current	I_C	–4	A
Collector peak current	$I_{C(peak)}$	–8	A
Collector power dissipation	P_C*[1]	40	W
Junction temperature	Tj	150	°C
Storage temperature	Tstg	–45 to +150	°C

Note: 1. Value at T_C = 25°C

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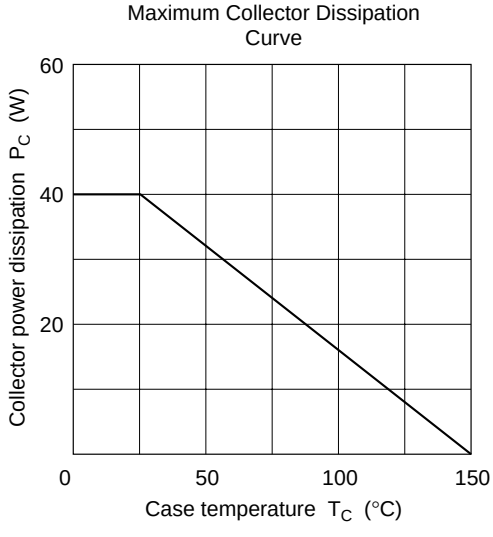
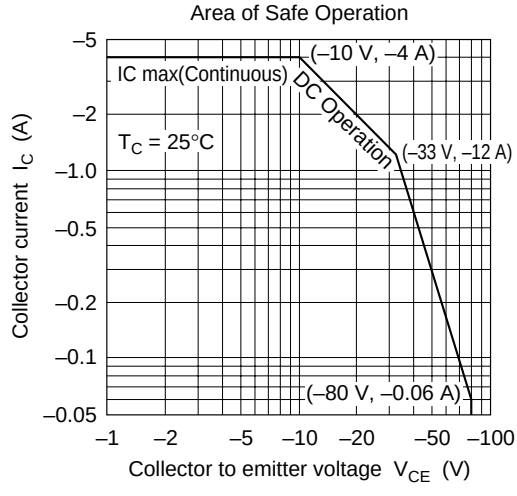
Electrical Characteristics (Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test conditions
Collector to emitter breakdown voltage	$V_{(BR)CEO}$	–80	—	—	V	I_C = –50 mA, R_{BE} = ∞
Emitter to base breakdown voltage	$V_{(BR)EBO}$	–5	—	—	V	I_E = –10 µA, I_C = 0
Collector cutoff current	I_{CBO}	—	—	–0.1	mA	V_{CB} = –80 V, I_E = 0
DC current transfer ratio	h_{FE1}*[1]	60	—	200		V_{CE} = –5 V, I_C = –1 A*[2]
	h_{FE2}	35	—	—		V_{CE} = –5 V, I_C = –0.1 A*[2]
Base to emitter voltage	V_{BE}	—	—	–1.5	V	V_{CE} = –5 V, I_C = –1 A*[2]
Collector to emitter saturation voltage	$V_{CE(sat)}$	—	—	–2	V	I_C = –2 A, I_B = –0.2 A*[2]
Gain bandwidth product	f_T	—	20	—	MHz	V_{CE} = –5 V, I_C = –0.5 A*[2]
Collector output capacitance	Cob	—	75	—	pF	V_{CB} = –20 V, I_E = 0, f = 1 MHz

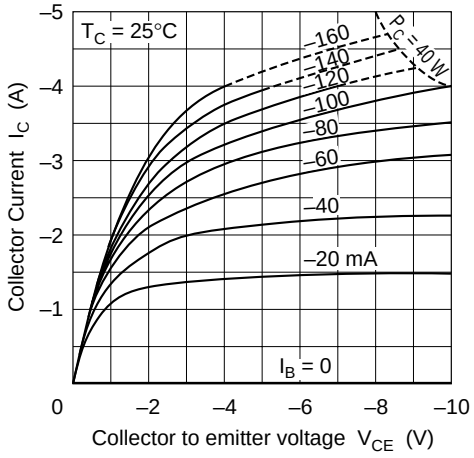
Notes: 1. The 2SB859 is grouped by h_{FE1} as follows.
2. Pulse test

B	C
60 to 120	100 to 200

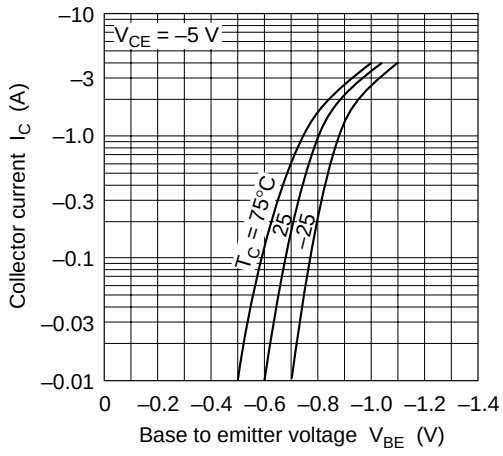




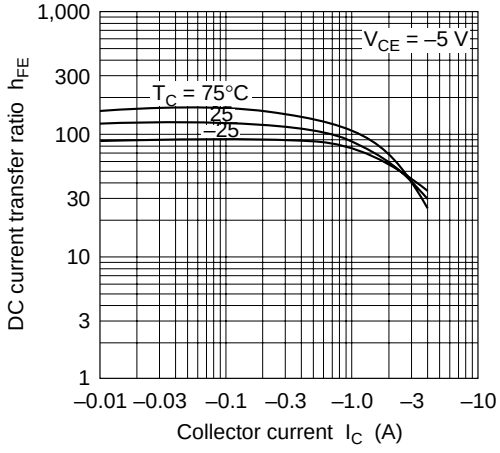
Typical Output Characteristics



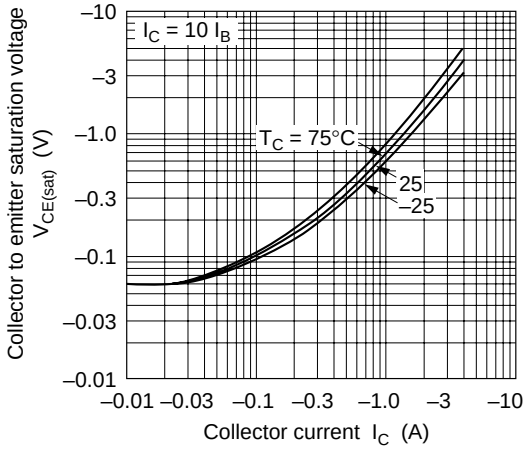
Typical Transfer Characteristcs



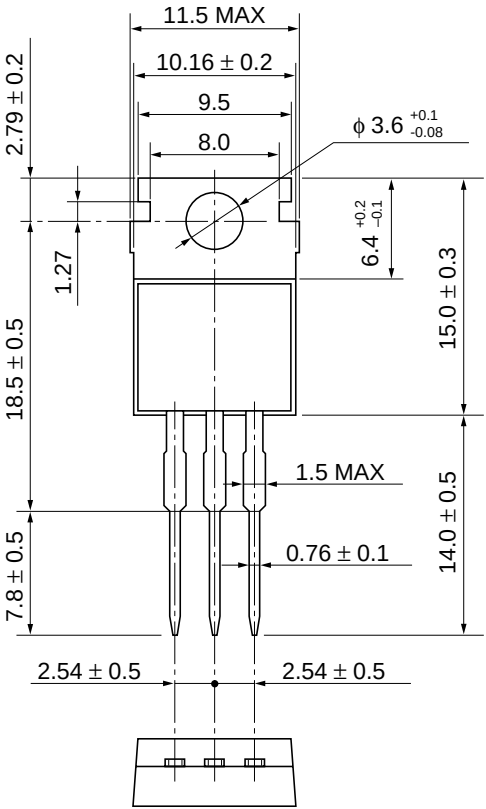
DC Current Transfer Ratio vs. Collector Current

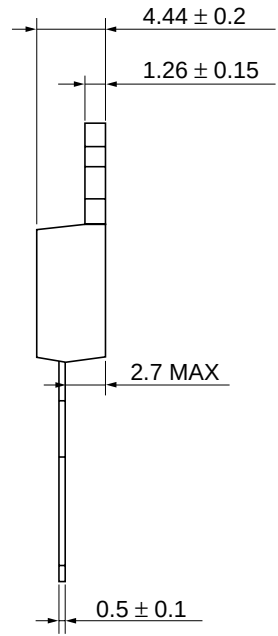


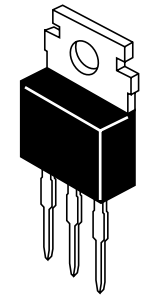
Collector to Emitter Saturation Voltage vs. Collector Current



Unit: mm







Hitachi Code	TO-220AB
JEDEC	Conforms
EIAJ	Conforms
Weight (reference value)	1.8 g

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HITACHI

Hitachi, Ltd.
Semiconductor & Integrated Circuits.
Nippon Bldg., 2-6-2, Ohte-machi, Chiyoda-ku, Tokyo 100-0004, Japan
Tel: Tokyo (03) 3270-2111 Fax: (03) 3270-5109

URL
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For further information write to:

Hitachi Semiconductor
(America) Inc.
179 East Tasman Drive,
San Jose,CA 95134
Tel: <1> (408) 433-1990
Fax: <1>(408) 433-0223

Hitachi Europe GmbH
Electronic components Group
Dornacher Straße 3
D-85622 Feldkirchen, Munich
Germany
Tel: <49> (89) 9 9180-0
Fax: <49> (89) 9 29 30 00

Hitachi Europe Ltd.
Electronic Components Group.
Whitebrook Park
Lower Cookham Road
Maidenhead
Berkshire SL6 8YA, United Kingdom
Tel: <44> (1628) 585000
Fax: <44> (1628) 778322

Hitachi Asia Pte. Ltd.
16 Collyer Quay #20-00
Hitachi Tower
Singapore 049318
Tel: 535-2100
Fax: 535-1533

Hitachi Asia Ltd.
Taipei Branch Office
3F, Hung Kuo Building. No.167,
Tun-Hwa North Road, Taipei (105)
Tel: <886> (2) 2718-3666
Fax: <886> (2) 2718-8180

Hitachi Asia (Hong Kong) Ltd.
Group III (Electronic Components)
7/F., North Tower, World Finance Centre,
Harbour City, Canton Road, Tsim Sha Tsui,
Kowloon, Hong Kong
Tel: <852> (2) 735 9218
Fax: <852> (2) 730 0281
Telex: 40815 HITEC HX